

The European Conference on Silicon Carbide and Related Materials (ECSCRM2016)

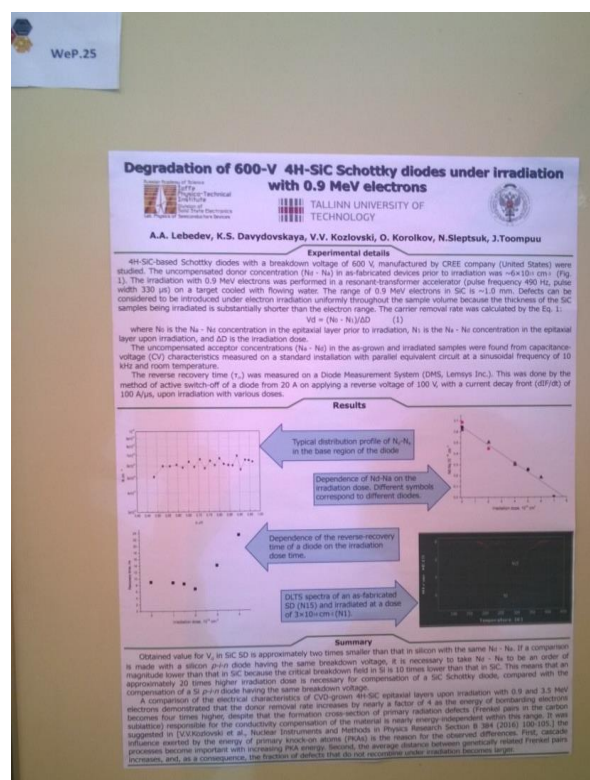
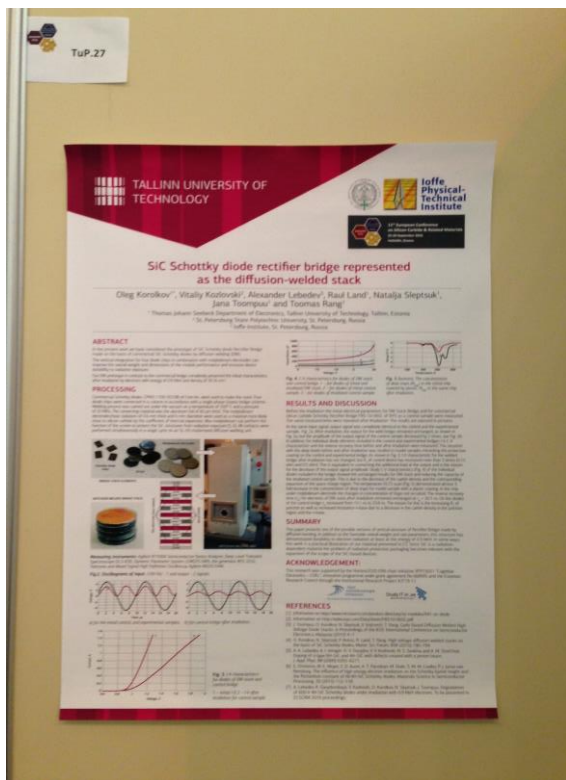
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The conference I participated in, is the most important technical conference series in the world for electronics devices technology based on silicon carbide (SiC) and related materials. At the following conference the number of participants was about 350 persons from all over the world – from universities, research centers and international companies. During the conference there were a lot of opportunities to meet the new people for possible future collaboration.

At the conference I with my colleague presented two posters:



Poster 1. SiC Schottky diode rectifier bridge represented as the diffusion-welded stack (the continuation of the research work from the previous paper presented at ICSCRM2015)

Poster 2. Degradation of 600-V 4H-SiC diodes under irradiation with 0,9MeV electrons. (investigation of irradiation influence on Schottky diodes –joined research work)

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The second poster has been performed within the cooperation with the St. Petersburg IOFFE Physico-Technical Institute that has been started from the meeting at the previous conference ICSCRM2015 (International Conference on Silicon Carbide and Related Materials).

During the poster presentations we had a large interest to our research work from Fraunhofer Institute (Germany), St. Petersburg State Electrotechnical University „LETI“ (Russia), Avangard company (Russia), Nitride Crystals company (USA) etc. The participation at the following conference helped a lot to strengthen the previous cooperations and make possible new ones. In personal, participation at such conferences of international level increases very much the chances to find people for future collaboration. Hope they have a possibility to participate for the next year as well.